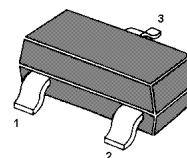
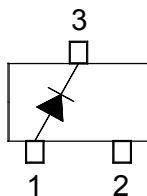


## SILICON EPITAXIAL PLANAR DIODE

### Band Switching Diode

For VHF band switching applications



Marking Code: **JC**  
SOT-23 Plastic Package

### Absolute Maximum Ratings ( $T_a = 25\text{ }^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Reverse Voltage	$V_R$	35	V
Forward Power Dissipation	$P_D$	200	mW
Junction Temperature	$T_j$	125	$^\circ\text{C}$
Storage Temperature Range	$T_s$	- 55 to + 150	$^\circ\text{C}$

### Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
Reverse Voltage at $I_R = 10\text{ }\mu\text{A}$	$V_R$	35	-	V
Reverse Current at $V_R = 25\text{ V}$	$I_R$	-	0.1	$\mu\text{A}$
Total Capacitance at $V_R = 20\text{ V}$ , $f = 1\text{ MHz}$	$C_T$	-	1	pF
Series Resistance at $I_F = 10\text{ mA}$ , $f = 100\text{ MHz}$	$r_s$	-	0.7	$\Omega$

### TYPICAL CHARACTERISTICS

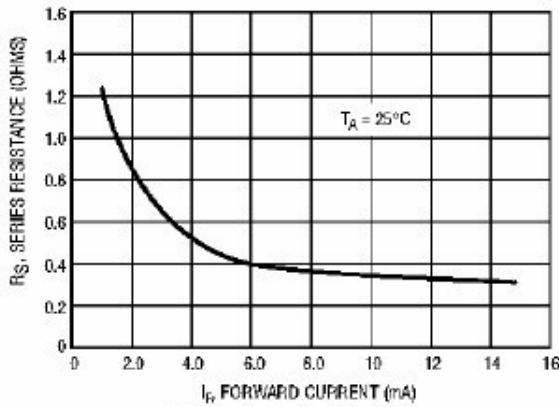


Figure 1. Series Resistance

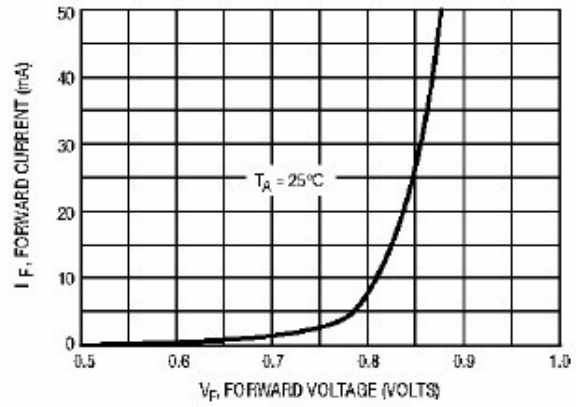


Figure 2. Forward Voltage

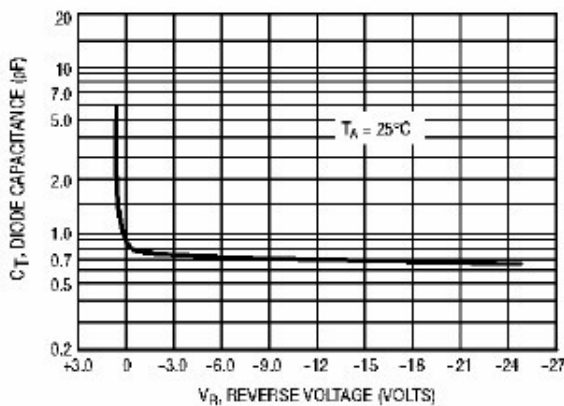


Figure 3. Diode Capacitance

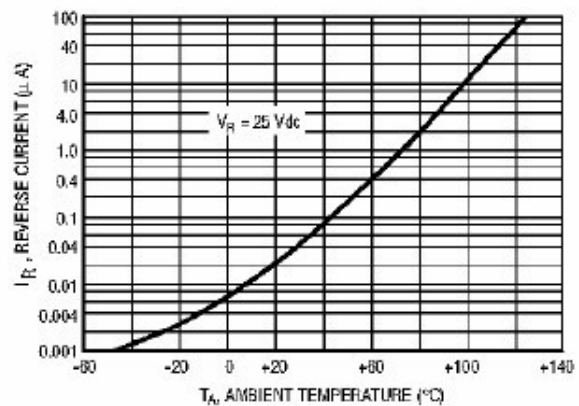


Figure 4. Leakage Current